

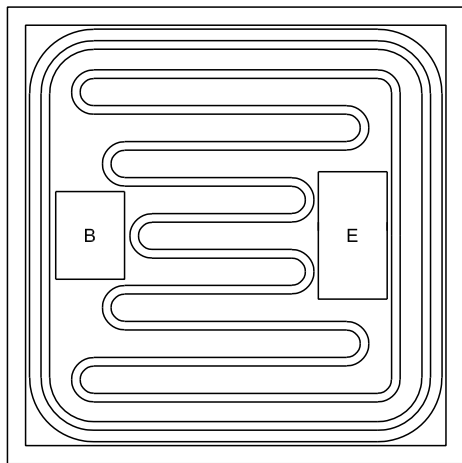
PROCESS CP734V
Small Signal Transistors
PNP - Chopper Transistor Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	31.5 x 31.5 MILS
Die Thickness	7.0 MILS
Base Bonding Pad Area	4.7 x 6.7 MILS
Emitter Bonding Pad Area	4.7 x 8.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 5 INCH WAFER

16,986

PRINCIPAL DEVICE TYPES

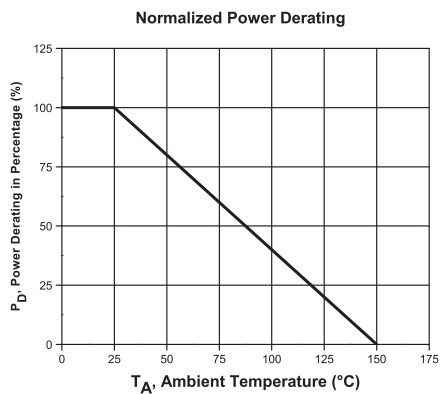
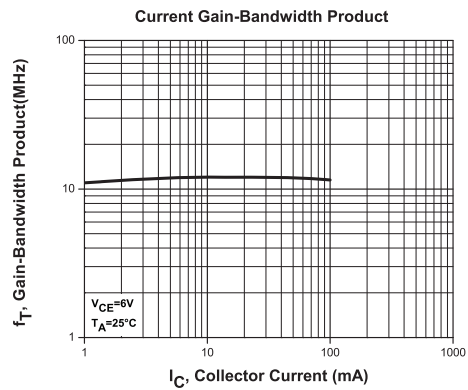
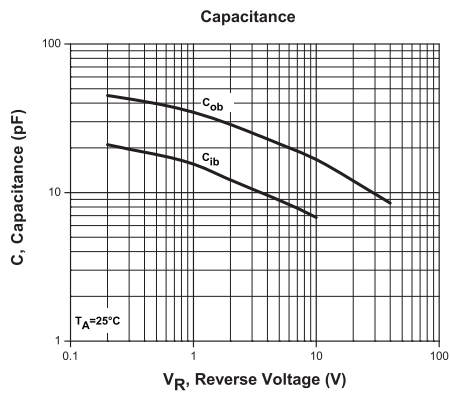
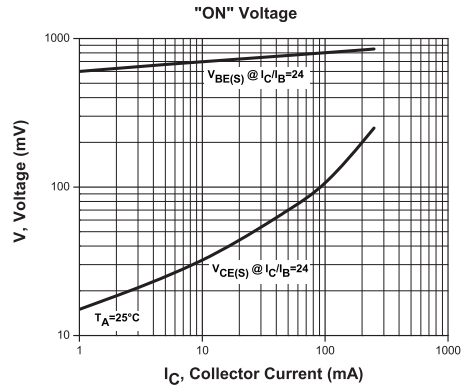
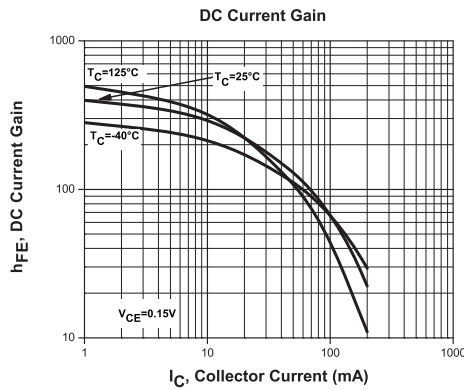
CMPT404A

MPS404A

R2 (22-March 2010)

PROCESS CP734V

Typical Electrical Characteristics



R2 (22-March 2010)